

IN THE SPECIFICATION:

Please replace the paragraphs at page 15, line 17 - page 16, line 2 with the following amended paragraphs:

As shown in FIG. 6A, when the bipolar carrier generation 601 is formed from a single material, a semiconductor (e.g., an intrinsic semiconductor) having a wide band gap in which electrons are located in a conduction band and holes are located in a valence band, a redox polymer which can perform both oxidation and reduction can be considered. In addition, the reference numerals ~~[[601]]~~ 610 and 611 in FIGS. 6A-C denote electroluminescent layers.

The concrete examples of the semiconductors having wide band gaps include III-group-N compounds such as GaN, AlN, BN, AlGa_xN_{1-x}, InGa_xN_{1-x}, and InAlGa_xN_{1-x}, II-VI group compounds ZnS, MgS, ZnSe, MgSe, ZnMgS_{1-x}Se_x, CdS, ZnO, and BeO, diamond, SiC, ZnGaS_{1-x}Se_x, CaF₂, and AlP ~~, and so on.~~ Furthermore, redox polymers include emeraldine base polyaniline (EB-PAni) ~~, and so on.~~